Abstracts

A physical large signal Si MOSFET model for RF circuit design

M.C. Ho, K. Green, R. Culbertson, J.Y. Yang, D. Ladwig and P. Ehnis. "A physical large signal Si MOSFET model for RF circuit design." 1997 MTT-S International Microwave Symposium Digest 2. (1997 Vol. II [MWSYM]): 391-394.

A new physically based Si MOSFET large signal model, BSIM3v3, developed by UC Berkeley, has been evaluated for high-frequency mixed-signal circuit analysis in a frequency domain, harmonic balance simulator. The model is validated using simulated RF power characteristics of automatic load pull measurement at different bias and matching conditions.

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